



TM0072P03NF

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

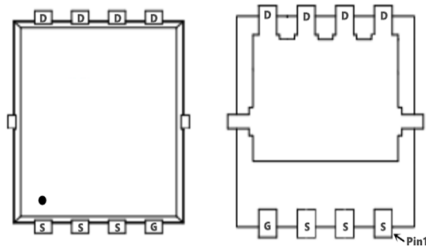
Applications

- Load switch
- PWM

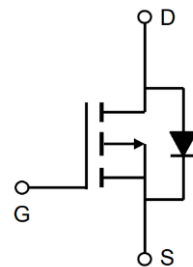
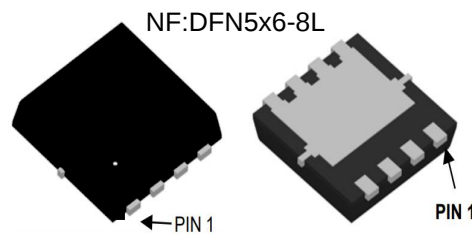
General Features

 $V_{DS} = -30V$ $I_D = -60A$ $R_{DS(ON)} = 7.2m\Omega(\text{typ.}) @ V_{GS} = -10V$

100% UIS Tested

100% R_g Tested

Marking: 60P03

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	-60	A
	$T_C = 100^\circ\text{C}$		-35	
Pulsed Drain Current ¹		I_{DM}	-168	A
Single Pulse Avalanche Energy ²		EAS	45	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	45	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	65	$^\circ\text{C/W}$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	3.36	$^\circ\text{C/W}$

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Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	-	-	V
Gate-body Leakage current		I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	$T_J=25^{\circ}C$	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1	μA
	$T_J=100^{\circ}C$			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-	-2.5	V
Drain-Source On-Resistance ⁴		$R_{DS(on)}$	$V_{GS} = -10V, I_D = -30A$	-	7.2	9.0	mΩ
			$V_{GS} = -4.5V, I_D = -15A$	-	10	18	
Forward Transconductance ⁴		g_{fs}	$V_{DS} = -5V, I_D = -30A$	-	57	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$	-	2396	-	pF
Output Capacitance		C_{oss}		-	325	-	
Reverse Transfer Capacitance		C_{rss}		-	283	-	
Gate Resistance		R_g	$f = 1MHz$	-	10.5	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q_g	$V_{GS} = -10V, V_{DS} = -15V, I_D = -30A$	-	30	-	nC
Gate-Source Charge		Q_{gs}		-	5	-	
Gate-Drain Charge		Q_{gd}		-	7.5	-	
Turn-On Delay Time		$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -15V, R_G = 3\Omega, I_D = -30A$	-	14.1	-	ns
Rise Time		t_r		-	20	-	
Turn-Off Delay Time		$t_{d(off)}$		-	94	-	
Fall Time		t_f		-	65	-	
Body Diode Reverse Recovery Time		t_{rr}	$I_F = -30A, di/dt = 100A/\mu s$	-	19	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}		-	9	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V_{SD}	$I_S = -1A, V_{GS} = 0V$	-	-	-1.2	V
Continuous Source Current	$T_C=25^{\circ}C$	I_S	-	-	-	-60	A

Note :

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD} = -25V, V_{GS} = -10V, L = 0.1mH, I_{AS} = -30A$.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

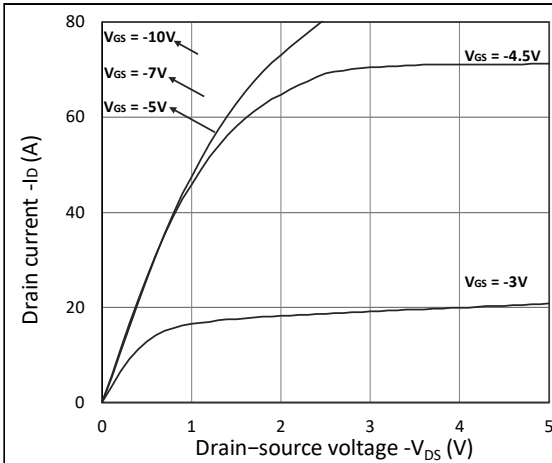


Figure 1. Output Characteristics

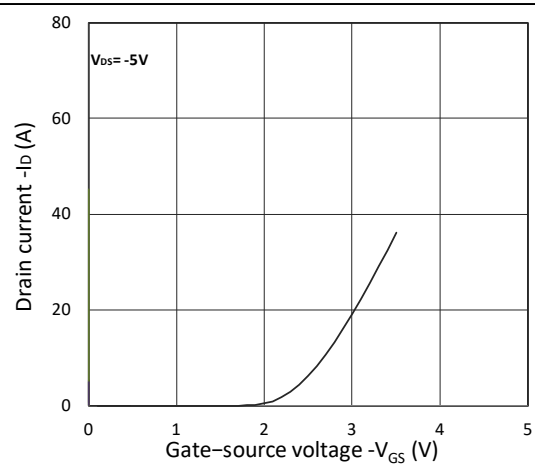


Figure 2. Transfer Characteristics

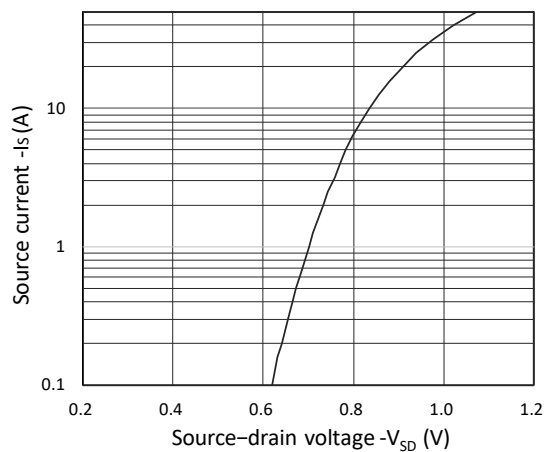
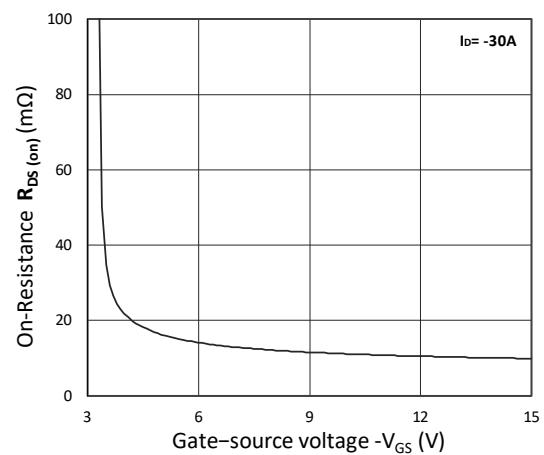
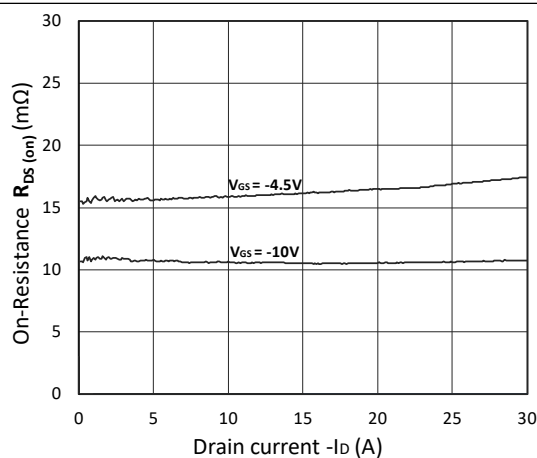
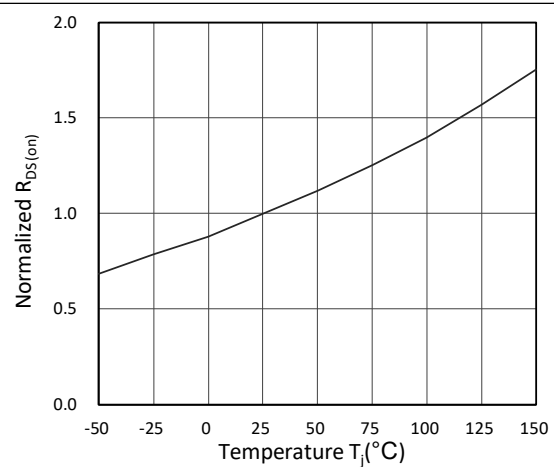


Figure 3. Forward Characteristics of Reverse

Figure 4. $R_{DS(on)}$ vs. V_{GS} Figure 5. $R_{DS(on)}$ vs. I_D Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

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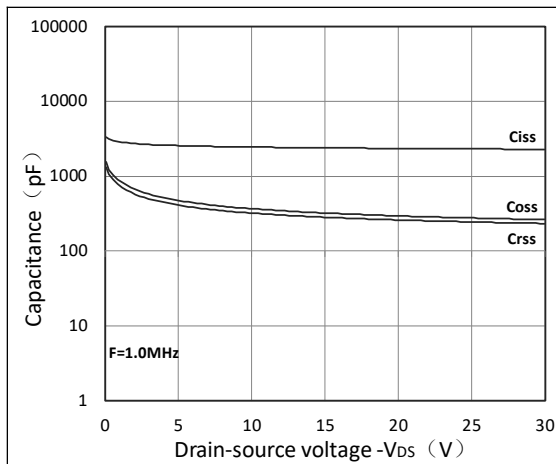


Figure 7. Capacitance Characteristics

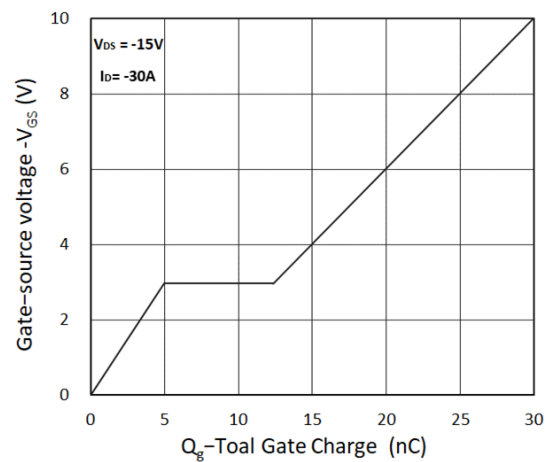


Figure 8. Gate Charge Characteristics

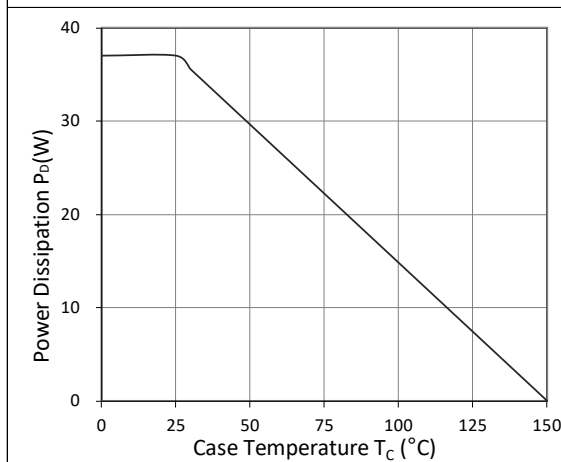


Figure 9. Power Dissipation

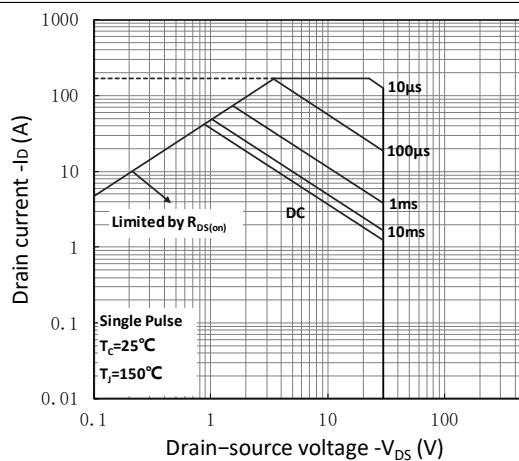


Figure 10. Safe Operating Area

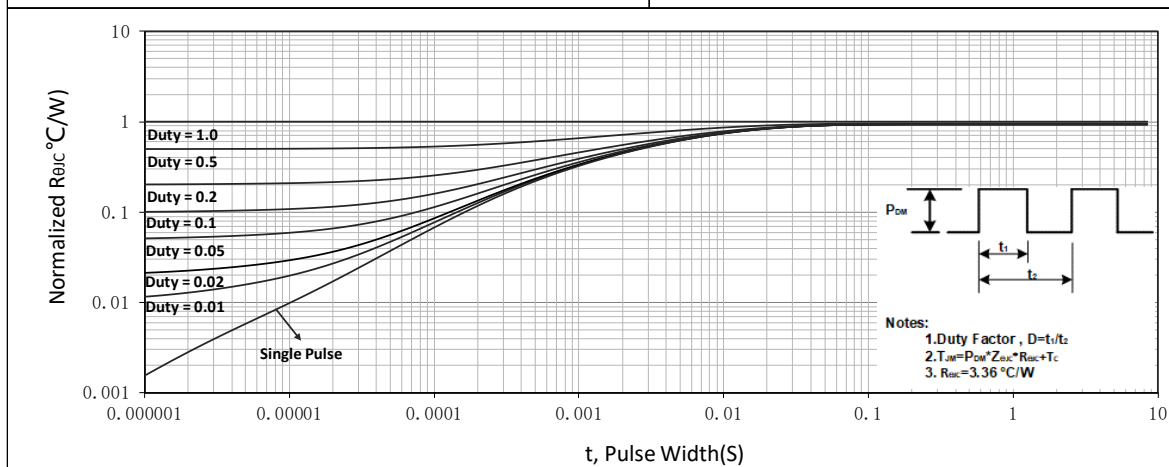
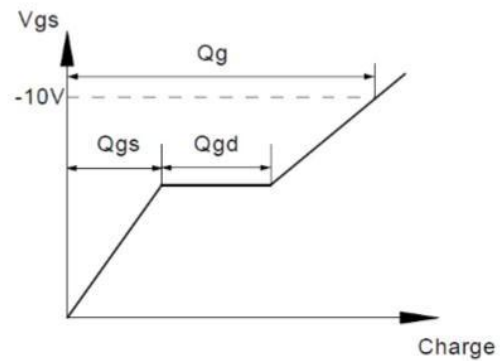
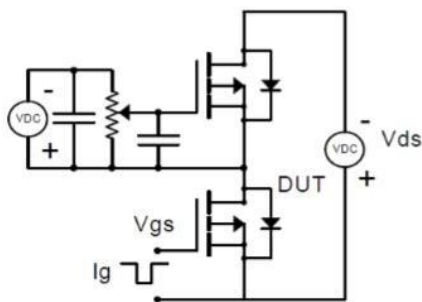


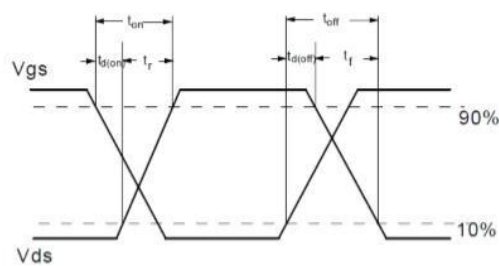
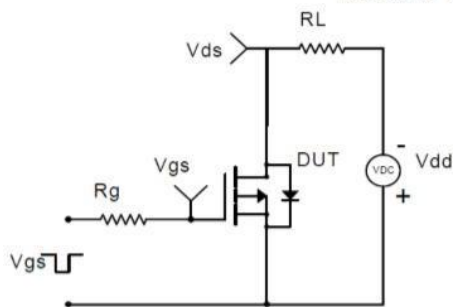
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

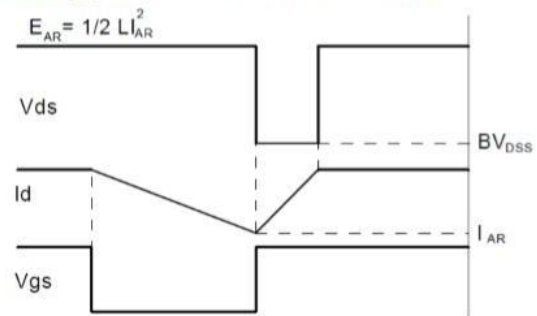
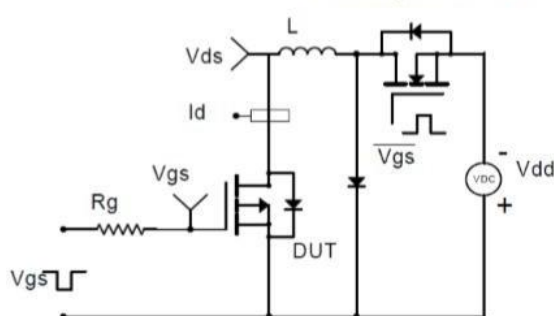
Gate Charge Test Circuit & Waveform



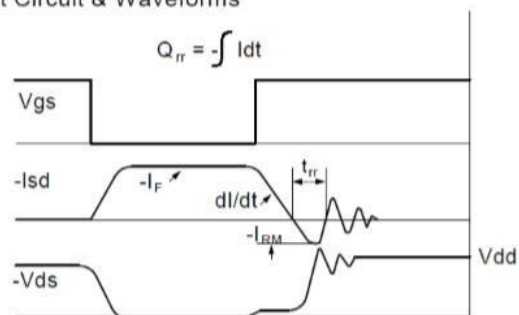
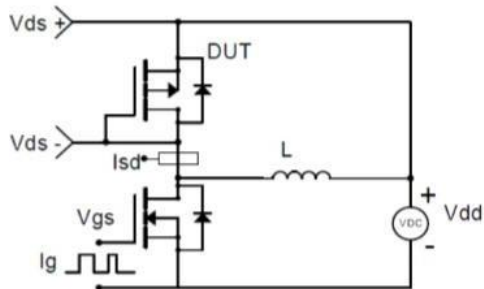
Resistive Switching Test Circuit & Waveforms



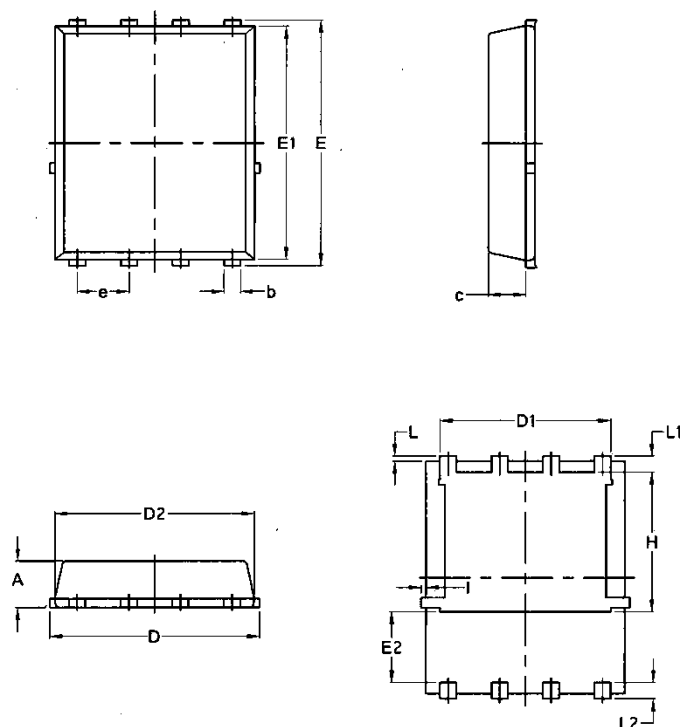
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data: DFN5x6-8L



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070